nexperia

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier		User Part Number						
Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		PDTC144EMB						
		Part Description						
		Nexperia DHAM Small Signal Bipolar Transistor MCD package						
								Test Conditions
			TEST					
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
	PC	Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85%	24 hours 168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	208	16640	0		
# AI	Treconditioning	MIL-STD-750-1	5 cycles	208	10040	0		
	HTRB	MIL-STD-750-1 M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
		5	1000 110010	202	10100	0		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	52	4160	0		
		JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	52	4160	0		
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias	rated reverse voltage ¹¹	1000 hours	52	4160	0		
		MIL-STD-750 Method 1037						
	IOL	ton = toff, devices powered to insure ΔTj =						
# A5	Intermittent Operating Life	100 °C for 15000 cycles	1000 hours	52	4160	0		
	RSH Begistance to Solder Heat	JESD22-A111 260 °C ± 5 °C	10					
# C8	Resistance to Solder Heat	200 ~ C = 3 ~ C	10 s	n.a.	n.a.	n.a.		
	SD Soldorability	J-STD-002				•		
# C10	Solderability	J-51D-002		111	1110	0		

[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia DHAM	Small Signal Bipolar Transistor	16160	0	0.26	3.81E+09

© 2022 Nexperia B.V.

All information hereunder is per Nexperia's best knowledge. This document does not provide for any nexperia.com representation or warranty express or implied by Nexperia. In case Nexperia has tested the product, this documentation reflects the outcome of the analysis of the actually tested parts only.